

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 04-100292

(43)Date of publication of application : 02.04.1992

(51)Int.Cl.

H01S 3/18

(21)Application number : 02-218622

(71)Applicant : FUJITSU LTD

(22)Date of filing : 20.08.1990

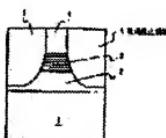
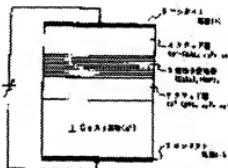
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## (54) SEMICONDUCTOR LASER

### (57)Abstract:

PURPOSE: To obtain a semiconductor laser composed of a direct transition type superlattice active layer and a clad layer having almost complete lattice matching for the active layer, by providing a double hetero junction wherein an active layer is constituted of a superlattice layer formed by alternately laminating III-V compound of direct transition type and that of indirect transition type, and a clad layer is constituted of III-V compound which has macroscopically almost the same composition as the superlattice layer.

CONSTITUTION: A clad layer 2 of  $N\text{-GaAs}_{0.52}\text{P}_{0.48}$  is epitaxially grown on an  $N\text{-GaAs}$  substrate 1 by a usual vapor growth method. The layer is a carrier confinement layer, and at the same time a buffer layer for growing a desired superlattice layer on the GaAs substrate. By ALE of MOCVD, one-atomic layers of GaAs and one-atomic layers of GaP are alternately grown, and a superlattice layer 3 is formed, on which a clad layer 4 of  $P\text{-GaAs}_{0.52}\text{P}_{0.48}$  is grown by an ordinary vapor growth method. Said layer is a carrier confinement layer, and a contact layer for forming an electrode is formed on the upermost surface. By mesa etching, the width of the active region is limited to be a specified value. After a buried layer 5 being a current blocking region is formed by liquid growth, electrodes 6 and 7 are formed, thereby completing a superlattice semiconductor laser.



## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]